MBR2535CTG, MBR2545CTG

Switch-mode Power Rectifiers

The MBR2535CTG/45CTG series uses the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- These are Pb-Free Devices*

Mechanical Characteristics

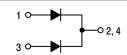
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER RECTIFIERS 30 AMPERES 35 and 45 VOLTS





TO-220 CASE 221A STYLE 6

MARKING DIAGRAM



A = Assembly Location Y = Year

WW = Work Week
B25x5 = Device Code
x = 3 or 4

G = Pb-Free Package AKA = Diode Polarity

ORDERING INFORMATION

Device	Package	Shipping
MBR2535CTG	TO-220 (Pb-Free)	50 Units/Rail
MBR2545CTG	TO-220 (Pb-Free)	50 Units/Rail

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR2535CTG, MBR2545CTG

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBR2535CTG MBR2545CTG	V _{RRM} V _{RWM} V _R	35 45	V	
Average Rectified Forward Current (Rated V_R , $T_C = 160^{\circ}C$) Per Device Per Diode	I _{F(AV)}	30 15	А	
Peak Repetitive Forward Current per Diode Leg (Rated V _R , Square Wave, 20 kHz, T _C = 150°C)		30	А	
Non-Repetitive Peak Surge Current per Diode Leg (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	А	
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I _{RRM}	1.0	Α	
Storage Temperature Range	T _{stg}	-65 to +175	°C	
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C	
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs	
ESD Ratings: Machine Model = C Human Body Model = 3B	ESD	> 400 > 8000	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient (Note 2)	R _{θJC} R _{θJA}	1.5 50	°C/W

^{2.} When mounted using minimum recommended pad size on FR-4 board.

ELECTRICAL CHARACTERISTICS (Per Diode)

Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _F	Instantaneous Forward Voltage (Note 3)	I _F = 15 Amp, T _J = 25°C I _F = 15 Amp, T _J = 125°C I _F = 30 Amp, T _J = 25°C I _F = 30 Amp, T _J = 125°C	1111	- 0.50 - 0.65	0.62 0.57 0.82 0.72	>
I _R	Instantaneous Reverse Current (Note 3)	Rated dc Voltage, T _J = 25°C Rated dc Voltage, T _J = 125°C		9.0	0.2 25	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

^{3.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

MBR2535CTG, MBR2545CTG

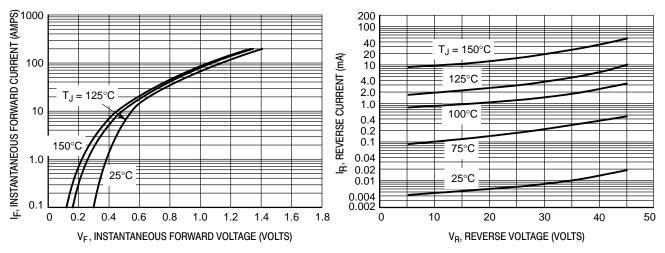


Figure 1. Typical Forward Voltage, Per Leg

Figure 2. Typical Reverse Current, Per Leg

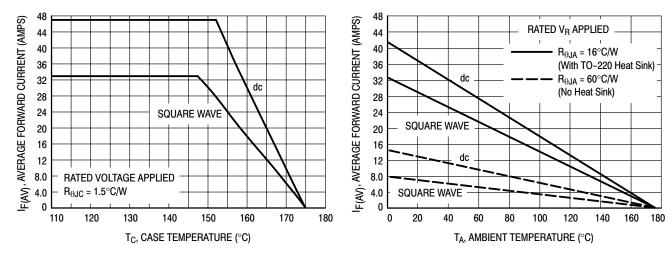


Figure 3. Current Derating, Per Device

Figure 4. Current Derating, Per Device

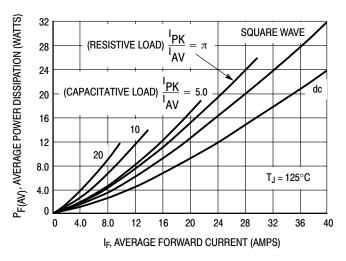


Figure 5. Forward Power Dissipation

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales